

SUPPORT FOR THE AMENDMENTS

The present amendment cancels claims 1-11, and adds new claims 12-35.

Support for newly added claim 12 is found at specification page 5, lines 23-24, page 6, lines 13-15, page 7, lines 18-31, page 8, lines 1-7, page 9, lines 14-17, as well as original claims 1-3.

Support for newly added claim 13 is found at specification page 9, lines 14-19, as well as original claims 8-9.

Support for newly added claims 14-15 is found at specification page 10, lines 30-31.

Support for newly added claims 16-17 is found at specification page 9, lines 19-20, as well as original claim 10.

Support for newly added claims 18-25 is found at specification page 8, lines 19-37, as well as original claims 4-7.

Support for newly added claims 26-28 is found at specification page 8, lines 9-17.

Support for newly added claims 29-30 is found at specification page 9, lines 7-12.

Support for newly added claim 31 is found at specification page 9, lines 14-15, and page 11, line 1.

Support for newly added claims 32-35 is found at specification page 9, lines 22-29, and page 11, line 11, as well as original claims 10 and 11.

It is believed that these amendments have not resulted in the introduction of new matter.

REMARKS

Claims 12-35 are currently pending in the present application. Claims 1-11 have been cancelled, and new claims 12-35 have been added, by the present amendment.

Applicants wish to extend their appreciation to Primary Examiner Geyer and Examiner Patel for the helpful and courteous discussion held on September 20, 2007, with their undersigned Representative. During the meeting, the prior art rejections were discussed. The content of this discussion is believed to be reflected in the remarks set forth herein.

The rejection of now cancelled claims 1, 3 and 8-11 under 35 U.S.C. § 102(b) as being anticipated over Huang (XP-002300511) is respectfully traversed, with respect to new claims 12-35.

Huang describes a process for producing a low dielectric film on a silicon wafer patterned with copper electrodes, wherein the process involves spin coating onto the silicon wafer a methyl silsesquioxane according to general formula  $(\text{MeSiO}_{3/2})_n$ , as exemplified by the structural formula set forth in Fig. 1 (See e.g., page 3677, column 1, lines 23-25, page 3678, column 1, Fig. 1, page 3679, column 1, lines 13-22).

Unlike the disclosure of Huang, the present invention is directed to a process for producing a low-k dielectric film deposited on a substrate, wherein the process involves coating the substrate with a solution comprising an incompletely condensed polyhedral oligomeric silsesquioxane according to structural formula (1) or (2), so as to produce a low-k dielectric film deposited on the substrate. The claimed silsesquioxanes of formula (1) and (2) are *structurally distinct* from, and thus not anticipated by, the silsesquioxane exemplified by the structural formula set forth in Fig. 1 of Huang.

Withdrawal of this ground of rejection is respectfully requested.

The rejection of now cancelled claims 1-7 under 35 U.S.C. § 102(e) as being anticipated over Jost (U.S. 2005/0010012) is respectfully traversed, with respect to new claims 12-35.

Applicants respectfully submit that Jost does not qualify as prior art under 35 U.S.C. § 102(e) since priority document WO 03/042223 was not published in English (See e.g., MPEP § 706.02(f)(1), Example 5 and III. Flowcharts). However, Jost could have been relied upon as the English language equivalent of WO 03/042223. Accordingly, the patentable distinction of the present invention over the disclosure of Jost is discussed herein.

Jost describes a process for producing a functionalized oligomeric silsesquioxane by reacting an incompletely condensed polyhedral oligomeric silsesquioxane with an alkoxysilane (See e.g., abstract, [0001], [0003], [0008], [0009], [0011], [0015], [0018], [0027], [0028], [0030]-[0032]). Jost further describes synthesizing and modifying/derivatizing a polymer with the functionalized oligomeric silsesquioxane to produce a resultant polymer, which is coated on an electronic material (See e.g., abstract, [0001], [0003], [0008], [0009], [0011], [0015], [0018], [0027], [0028], [0030]-[0032]).

In contrast, the claimed process involves coating the substrate with an incompletely condensed polyhedral oligomeric silsesquioxane, as opposed to the resultant polymer described in Jost. Therefore, the claimed process is *fundamentally different* from, and thus not anticipated by, the process described in Jost.

Withdrawal of this ground of rejection is respectfully requested.

In conclusion, Applicants submit that the present application is now in condition for allowance and notification to this effect is earnestly solicited.

Respectfully submitted,

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A handwritten signature in dark ink, appearing to read "David P. Stitzel", is written over a horizontal line.

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